New Product



SiA447DJ

RoHS

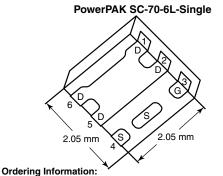
COMPLIANT

HALOGEN FREE

Vishay Siliconix

P-Channel 12 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (Ω) (Max.)	I _D (A)	Q _g (Typ.)		
- 12	0.0135 at V _{GS} = - 4.5 V	- 12 ^a			
	0.0194 at V _{GS} = - 2.5 V	- 12 ^a	31 nC		
	0.0344 at V _{GS} = - 1.8 V	- 12 ^a	31110		
	0.0710 at V _{GS} = - 1.5 V	- 3			



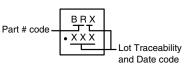
FEATURES

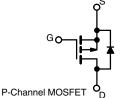
- TrenchFET[®] Power MOSFET
- Thermally Enhanced PowerPAK[®] SC-70 Package - Small Footprint Area
 - Low On-Resistance
- 100 % R_g Tested Material categorization:
- For definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Providing low voltage drop in Smart Phones, Tablet PCs, Mobile Computing:
 - Battery Switches
 - Battery Management
 - Load Switches

Marking Code





SiA447DJ-T4-GE3 (Lead (Pb)-free and Halogen-free) SiA447DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	- 12	V	
Gate-Source Voltage		V _{GS}	± 8	v	
	T _C = 25 °C		- 12 ^a		
Continuous Drain Current (T 150 °C)	T _C = 70 °C		- 12 ^a		
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	I _D	- 12 ^{a, b, c}		
	T _A = 70 °C		- 10 ^{b, c}	А	
Pulsed Drain Current (t = 300 μs)		I _{DM}	- 50		
Continuous Source-Drain Diode Current	T _C = 25 °C		- 12 ^a		
	T _A = 25 °C	I _S	- 2.9 ^{b, c}		
Maximum Power Dissipation	T _C = 25 °C		19		
	T _C = 70 °C		12	w	
	T _A = 25 °C	P _D	3.5 ^{b, c}	vv	
	T _A = 70 °C		2.2 ^{b, c}		
Operating Junction and Storage Temperature R	T _J , T _{stg}	- 55 to 150	°C		
Soldering Recommendations (Peak Temperatur	-	260			

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	28	36	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	5.3	6.5	0/11	

Notes:

a. Package limited

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b. Surface mounted on 1" x 1" FR4 board.

t = 5 s. c.

d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

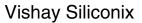
Rework conditions: manual soldering with a soldering iron is not recommended for leadless components. e.

Maximum under steady state conditions is 80 °C/W. f.

For more information please contact: pmostechsupport@vishay.com

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SiA447DJ





Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	Cymbol			Typ.	max.	Unit	
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = - 250 μA	- 12			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$			- 7		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = - 250 μA		3			
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 0.4	-	- 0.85		
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			± 100	nA	
	000	$V_{DS} = -12 V, V_{GS} = 0 V$			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 12 V, V _{GS} = 0 V, T _J = 55 °C			- 10	μA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 V, V_{GS} = -4.5 V$	- 10			А	
	·D(01)	V _{GS} = - 4.5 V, I _D = - 7 A		0.0110	0.0135	- Ω	
	_	V _{GS} = - 2.5 V, I _D = - 5 A		0.0150	0.0194		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 1.8 V, I _D = - 3 A		0.0230	0.0344		
		V _{GS} = - 1.5 V, I _D = - 1 A		0.0400	0.0710		
Forward Transconductance ^a	9 _{fs}	$V_{\rm DS} = -6 \text{ V}, \text{ I}_{\rm D} = -7 \text{ A}$		35		S	
Dynamic ^b	-10				1	I	
Input Capacitance	C _{iss}			2880			
Output Capacitance	C _{oss}	V _{DS} = - 6 V, V _{GS} = 0 V, f = 1 MHz		590		pF	
Reverse Transfer Capacitance	C _{rss}			585		1	
-	Q _g Q _{gs} Q _{gd}	V _{DS} = - 6 V, V _{GS} = - 8 V, I _D = - 13 A		52	80	1	
Total Gate Charge		V _{DS} = - 6 V, V _{GS} = - 4.5 V, I _D = - 13 A		31	47	nC	
Gate-Source Charge				4.2			
Gate-Drain Charge				7.8			
Gate Resistance	R _g	f = 1 MHz	0.8	4.3	8.6	Ω	
Turn-On Delay Time	t _{d(on)}			30	60		
Rise Time	t _r	$V_{DD} = -6 V, R_1 = 0.6 \Omega$		30	60	- ns	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 10 Å, V_{GEN} = - 4.5 V, R_g = 1 Ω		60	120		
Fall Time	t _f			25	50		
Turn-On Delay Time	t _{d(on)}			12	25		
Rise Time	t _r	V_{DD} = - 6 V, R_{L} = 0.6 Ω		10	20		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 10 Å, V_{GEN} = -8 V, R_g = 1 Ω		65	130		
Fall Time	t _f			20	40		
Drain-Source Body Diode Characterist				•			
Continuous Source-Drain Diode Current	۱ _S	T _C = 25 °C			- 12	^	
Pulse Diode Forward Current	I _{SM}			Ī	- 50	A	
Body Diode Voltage	V _{SD}	I _S = - 10 A, V _{GS} = 0		- 0.8	- 1.2	V	
Body Diode Reverse Recovery Time t _{rr}				25	50	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			7.5	15	nC	
Reverse Recovery Fall Time	t _a	I _F = - 10 A, dI/dt = 100 A/μs, T _J = 25 °C		8			
Reverse Recovery Rise Time	t.	t _b		17		ns	

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

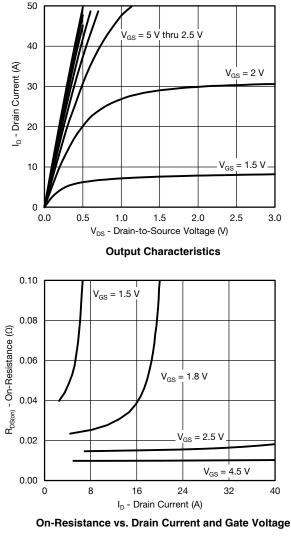
b. Guaranteed by design, not subject to production testing.

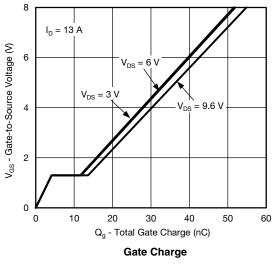
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

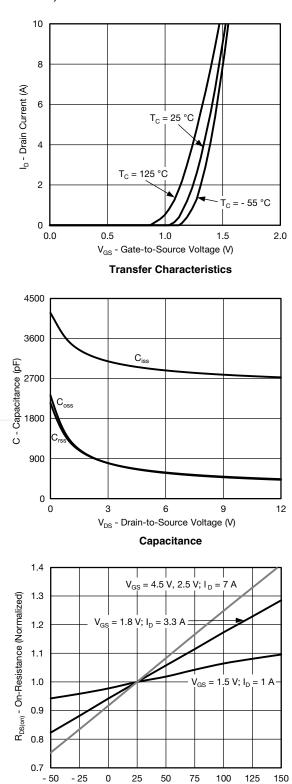


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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)







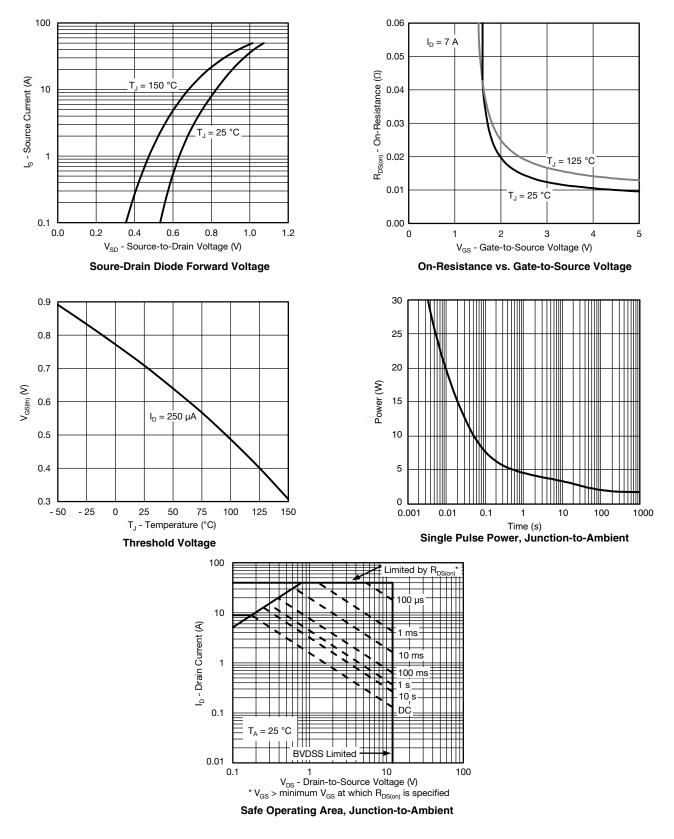
T_J - Junction Temperature (°C) **On-Resistance vs. Junction Temperature**

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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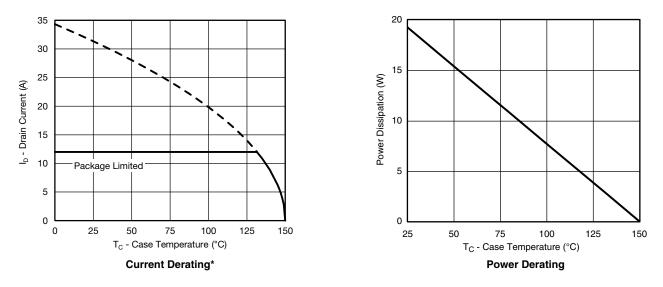
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



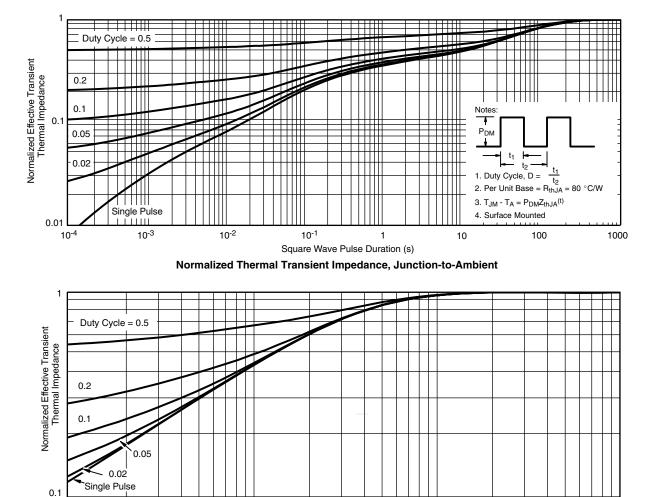
* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

SiA447DJ





TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



10⁻³ Square Wave Pulse Duration (s)

10⁻²

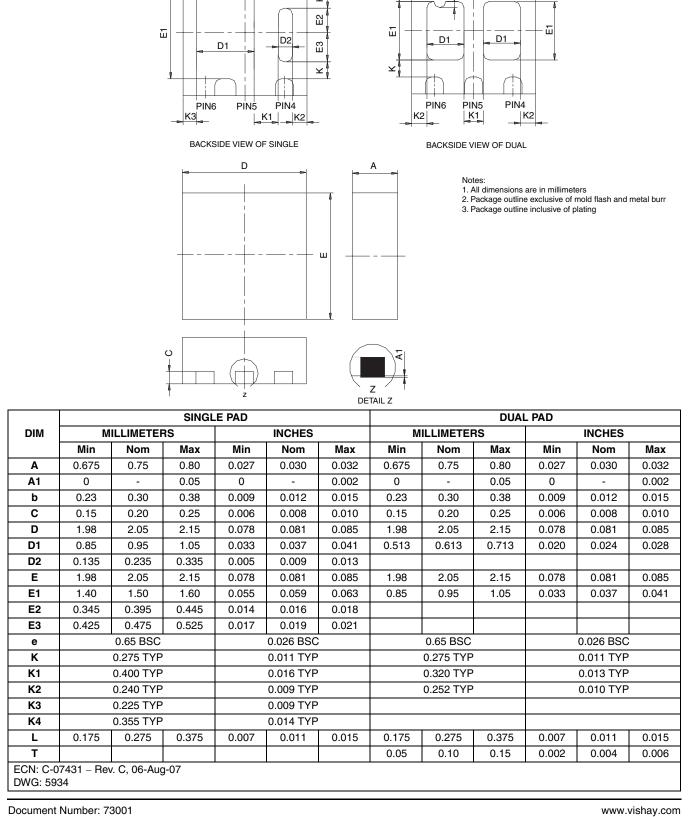
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63774.

10-4

10-1

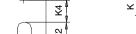
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PowerPAK[®] SC70-6L

VISHA

b PIN2 PIN1 PIN3 _ ₹



Package Information

b

PIN3

__ ₿

PIN2

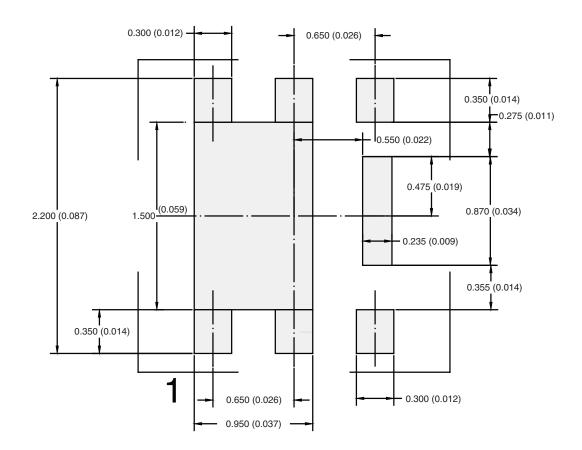
PIN1

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1



RECOMMENDED PAD LAYOUT FOR PowerPAK[®] SC70-6L Single



Dimensions in mm/(Inches)

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